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RFMD Introduces RF3482 Single-Chip Integrated Front End Module

GREENSBORO, N.C., Jun 29, 2010 (GlobeNewswire via COMTEX News Network) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies, today announced the availability of the RF3482 front end module (FEM). RFMD's highly integrated RF3482 single-chip FEM integrates a WiFi power amplifier with a single-pole, three-throw (SP3T) switch for 2.4 GHz to 2.5 Ghz ISM band applications.

By integrating the complete switch functionality, the RF3482 is able to route WiFi and Bluetooth(R) receive/transmit signals to two system-on-chip (SOC) transceivers, a typical design architecture implemented in a wide range of high-performance consumer electronics and handset/handheld WiFi applications. Additionally, the SP3T switch can act as a splitter to transmit or receive Bluetooth(R) and WLAN signals simultaneously.

The highly integrated RF3482 satisfies the need for aggressive size reductions for 802.11b/g front-end designs by realizing up to a 50% size reduction versus current discrete designs, while at the same time greatly reducing the number of components outside the core chipset. The RF3482 integrates a 2.5 GHz b/g power amplifier with 16dBm of linear output power for higher efficiency and lower EVM for 11n applications. The RF3482 also integrates 2170MHz filtering and harmonic attenuation, reducing the need for a high loss/attenuation filter at the FEM output and increasing the output power at the antenna. An integrated Rx balun eliminates the requirement for tuning components between the FEM and the SoC while the direct-to-battery connection eliminates the need for additional DC circuitry. The RF3482 is fully tested and is packaged in a small form factor 3.0 mm x 3.0 mm QFN package.

About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the cellular handset, wireless infrastructure, wireless local area network (WLAN), CATV/broadband and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at www.rfmd.com.

The RF Micro Devices, Inc. logo is available at http://www.globenewswire.com/newsroom/prs/?pkgid=6436

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including risks associated with the impact of global macroeconomic and credit conditions on our business and the business of our suppliers and customers, variability in operating results, the rate of growth and development of wireless markets, our reliance on inclusion in third party reference designs for a portion of our revenue, our ability to manage channel partner and customer relationships, risks associated with the operation of our wafer fabrication, molecular beam epitaxy, assembly and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, raw material costs and availability, our ability to reduce costs and improve margins in response to declining average selling prices, our ability to bring new products to market, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on a limited number of customers, dependence on gallium arsenide (GaAs) for the majority of our products, and dependence on third parties. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual

Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

SOURCE: RF Micro Devices

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